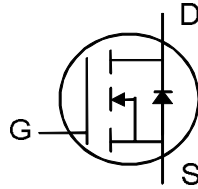


## N-CHANNEL ENHANCEMENT-MODE POWER MOSFET

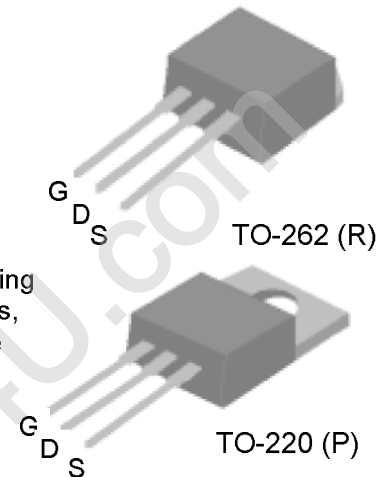
- Low gate-charge
- Simple drive requirement
- Fast switching



$BV_{DSS}$	600/650/700V
$R_{DS(ON)}$	2.4Ω
$I_D$	4A

### Description

The SSM04N70BR is in a TO-262 package, which is widely used for commercial and industrial applications, and is well suited for universal 90~265VAC off-line AC/DC converter applications. The SSM04N70BP is in the TO-220 package which has a mounting hole on the tab for attaching to a heat sink. These devices are manufactured with an advanced process, providing high blocking voltage to overcome voltage surge and sag in the toughest power systems with the best combination of fast switching, ruggedized design and cost-effectiveness.



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage - /-A/-H	600/650/700	V
$V_{GS}$	Gate-Source Voltage	± 30	V
$I_D @ T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	4	A
$I_D @ T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	2.5	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	15	A
$P_D @ T_C=25^{\circ}C$	Total Power Dissipation	62.5	W
	Linear Derating Factor	0.5	W/°C
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	100	mJ
$I_{AR}$	Avalanche Current	4	A
$E_{AR}$	Repetitive Avalanche Energy	4	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case Max.	2.0	°C/W
Rthj-a	Thermal Resistance Junction-ambient Max.	62	°C/W

**Electrical Characteristics @  $T_j=25^\circ\text{C}$  (unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$ / -	600	-	-	V
		$V_{GS}=0V, I_D=250\mu A$ / A	650	-	-	V
		$V_{GS}=0V, I_D=250\mu A$ / H	700	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	-	0.6	-	$\text{V}/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=2A$	-	-	2.4	$\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=2A$	-	2.5	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_j=25^\circ\text{C}$ )	$V_{DS}=600V, V_{GS}=0V$	-	-	10	$\mu\text{A}$
	Drain-Source Leakage Current ( $T_j=150^\circ\text{C}$ )	$V_{DS}=480V, V_{GS}=0V$	-	-	100	$\mu\text{A}$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 30V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>3</sup>	$I_D=4A$	-	16.7	-	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=480V$	-	4.1	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	4.9	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>3</sup>	$V_{DD}=300V$	-	11	-	ns
$t_r$	Rise Time	$I_D=4A$	-	8.3	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=10\Omega, V_{GS}=10V$	-	23.8	-	ns
$t_f$	Fall Time	$R_D=75\Omega$	-	8.2	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	950	-	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	65	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	6	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$I_S$	Continuous Source Current ( Body Diode )	$V_D=V_G=0V, V_S=1.5V$	-	-	4	A
$I_{SM}$	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	15	A
$V_{SD}$	Forward On Voltage <sup>3</sup>	$T_j=25^\circ\text{C}, I_S=4A, V_{GS}=0V$	-	-	1.5	V

**Notes:**

- Pulse width limited by safe operating area.
- Starting  $T_j=25^\circ\text{C}$ ,  $V_{DD}=50V$ ,  $L=25\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=4A$ .
- Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .

**Ordering Information**

SSM04N70BP, SSM04N70BR	$BV_{DSS} = 600V$
SSM04N70BP-A, SSM04N70BP-A	$BV_{DSS} = 650V$
SSM04N70BP-H, SSM04N70BP-H	$BV_{DSS} = 700V$

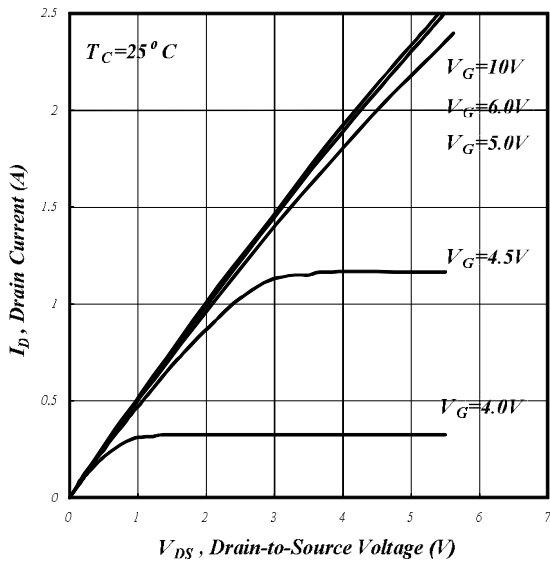


Fig 1. Typical Output Characteristics

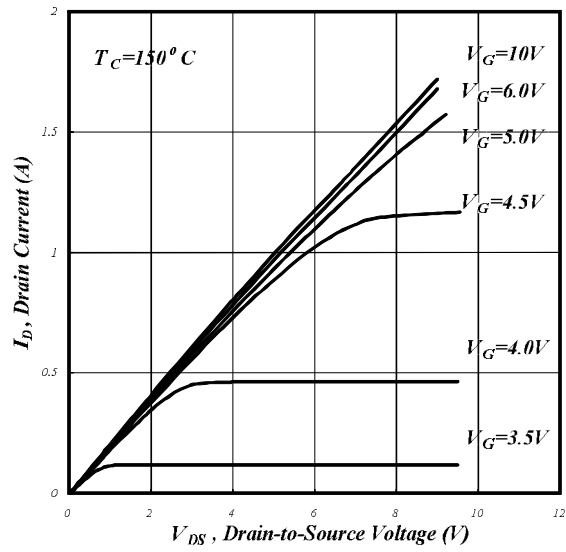


Fig 2. Typical Output Characteristics

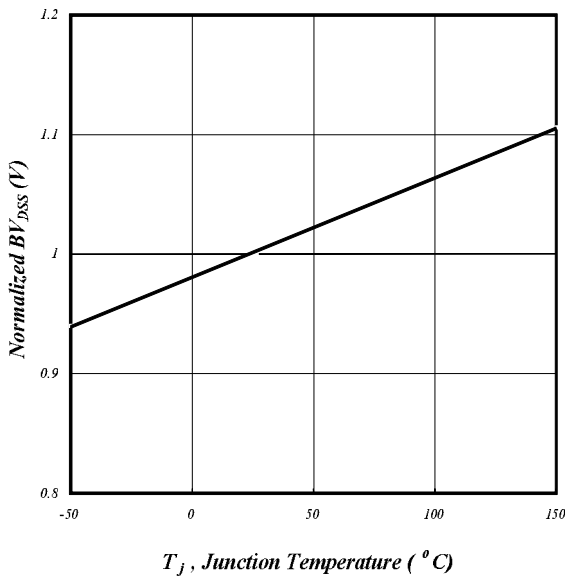


Fig 3. Normalized  $BV_{DSS}$  vs. Junction Temperature

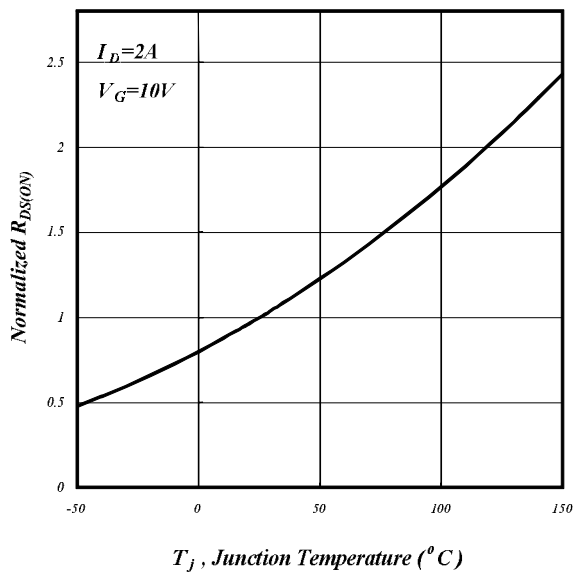


Fig 4. Normalized On-Resistance vs. Junction Temperature

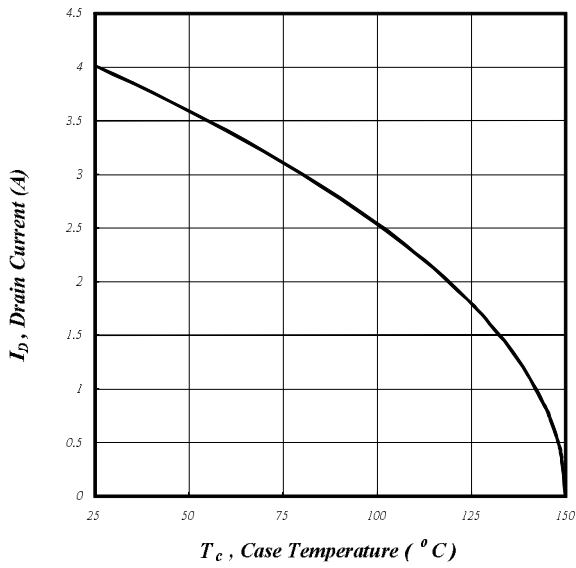


Fig 5. Maximum Drain Current vs. Case Temperature

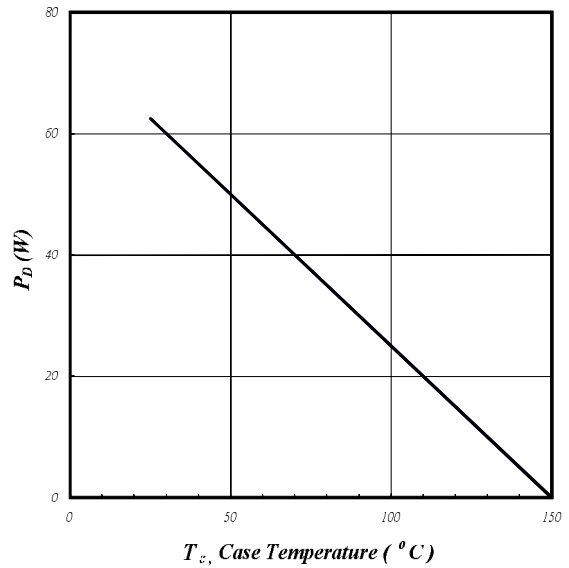


Fig 6. Typical Power Dissipation

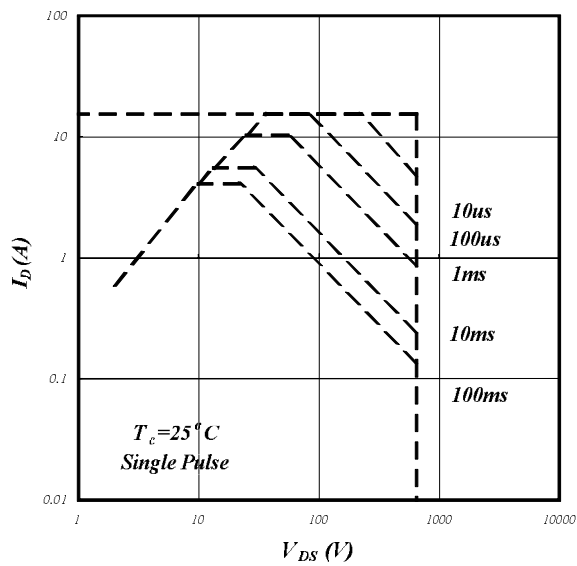


Fig 7. Maximum Safe Operating Area

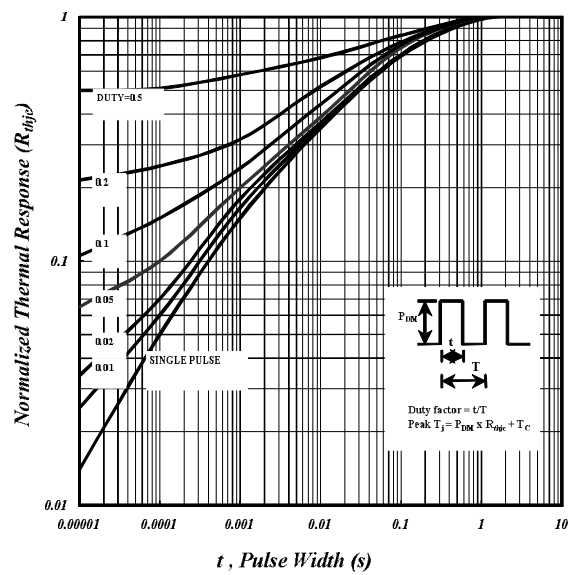


Fig 8. Effective Transient Thermal Impedance

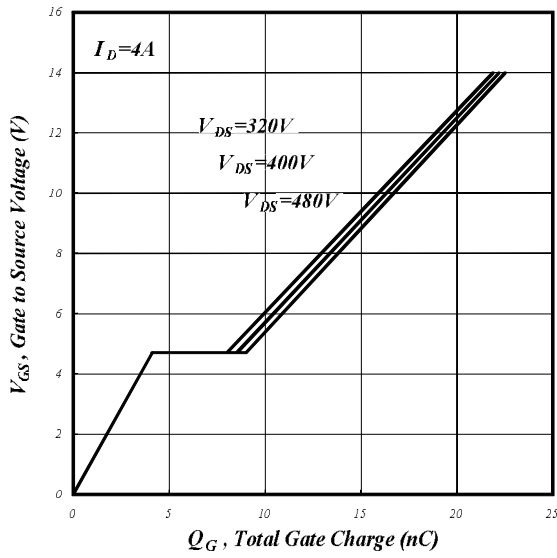


Fig 9. Gate Charge Characteristics

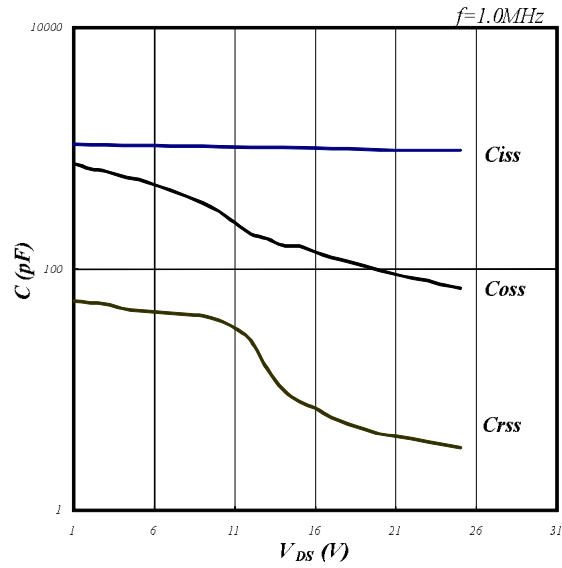


Fig 10. Typical Capacitance Characteristics

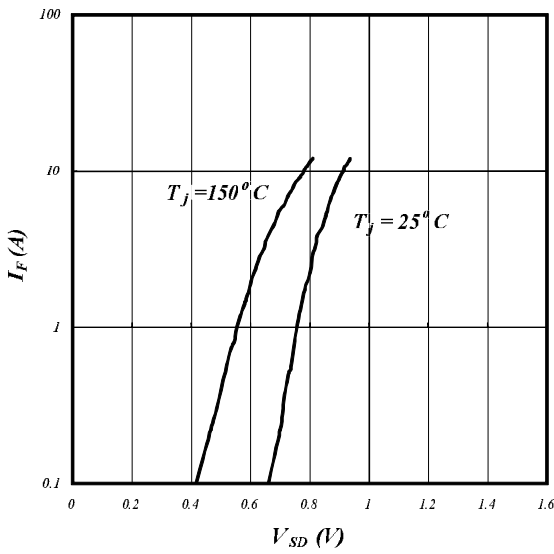


Fig 11. Forward Characteristic of Reverse Diode

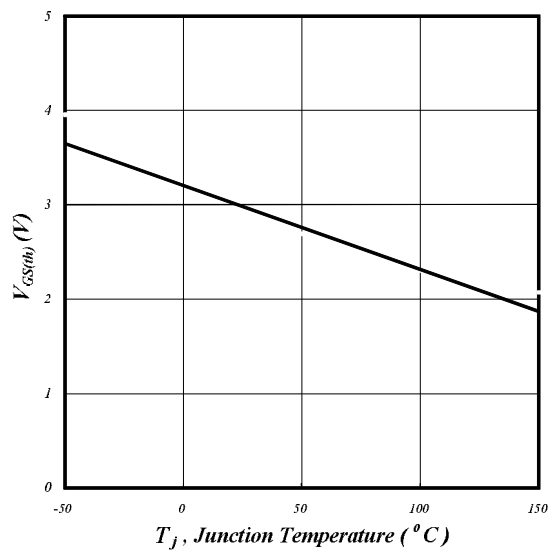


Fig 12. Gate Threshold Voltage vs. Junction Temperature

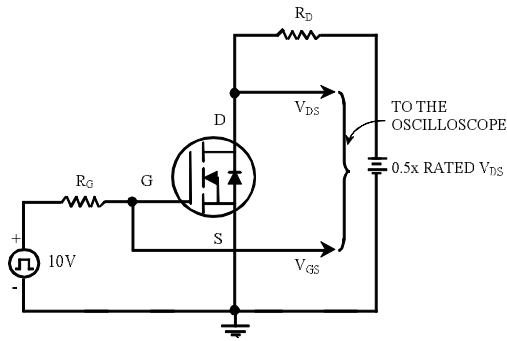


Fig 13. Switching Time Circuit

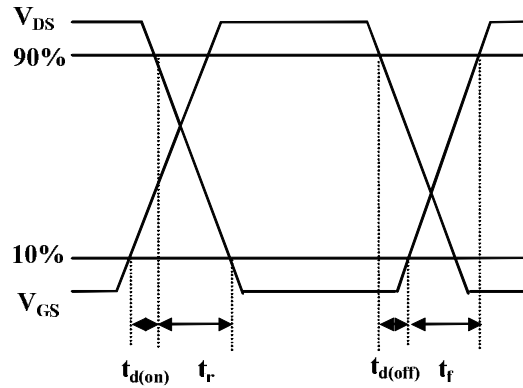


Fig 14. Switching Time Waveform

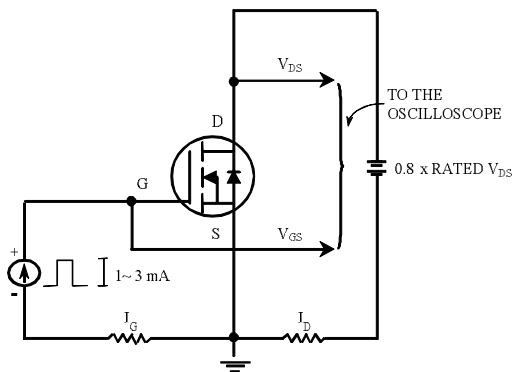


Fig 15. Gate Charge Circuit

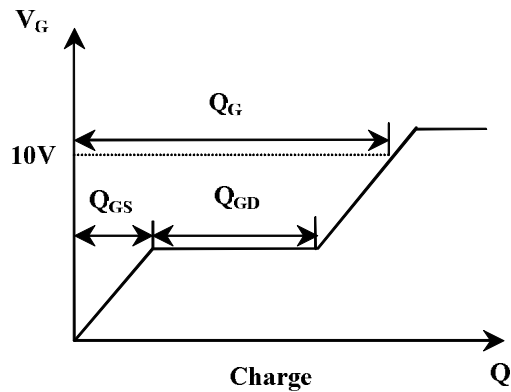


Fig 16. Gate Charge Waveform

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